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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	264
Number of Logic Elements/Cells	2112
Total RAM Bits	75776
Number of I/O	206
Number of Gates	-
Voltage - Supply	2.375V ~ 3.465V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-LFBGA
Supplier Device Package	256-CABGA (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo3lf-2100c-5bg256i

Features

■ Solutions

- Smallest footprint, lowest power, high data throughput bridging solutions for mobile applications
- Optimized footprint, logic density, IO count, IO performance devices for IO management and logic applications
- High IO/logic, lowest cost/IO, high IO devices for IO expansion applications

■ Flexible Architecture

- Logic Density ranging from 640 to 9.4K LUT4
- High IO to LUT ratio with up to 384 IO pins

■ Advanced Packaging

- 0.4 mm pitch: 1K to 4K densities in very small footprint WLCSP (2.5 mm x 2.5 mm to 3.8 mm x 3.8 mm) with 28 to 63 IOs
- 0.5 mm pitch: 640 to 6.9K LUT densities in 6 mm x 6 mm to 10 mm x 10 mm BGA packages with up to 281 IOs
- 0.8 mm pitch: 1K to 9.4K densities with up to 384 IOs in BGA packages

■ Pre-Engineered Source Synchronous I/O

- DDR registers in I/O cells
- Dedicated gearing logic
- 7:1 Gearing for Display I/Os
- Generic DDR, DDRx2, DDRx4

■ High Performance, Flexible I/O Buffer

- Programmable sysIO™ buffer supports wide range of interfaces:
 - LVCMOS 3.3/2.5/1.8/1.5/1.2
 - LVTTTL
 - LVDS, Bus-LVDS, MLVDS, LVPECL
 - MIPI D-PHY Emulated
 - Schmitt trigger inputs, up to 0.5 V hysteresis
- Ideal for IO bridging applications
- I/Os support hot socketing
- On-chip differential termination
- Programmable pull-up or pull-down mode

■ Flexible On-Chip Clocking

- Eight primary clocks
- Up to two edge clocks for high-speed I/O interfaces (top and bottom sides only)
- Up to two analog PLLs per device with fractional-n frequency synthesis
 - Wide input frequency range (7 MHz to 400 MHz)

■ Non-volatile, Multi-time Programmable

- Instant-on
 - Powers up in microseconds
- Optional dual boot with external SPI memory
- Single-chip, secure solution
- Programmable through JTAG, SPI or I²C
- MachXO3L includes multi-time programmable NVCM
- MachXO3LF infinitely reconfigurable Flash
 - Supports background programming of non-volatile memory

■ TransFR Reconfiguration

- In-field logic update while IO holds the system state

■ Enhanced System Level Support

- On-chip hardened functions: SPI, I²C, timer/counter
- On-chip oscillator with 5.5% accuracy
- Unique TraceID for system tracking
- Single power supply with extended operating range
- IEEE Standard 1149.1 boundary scan
- IEEE 1532 compliant in-system programming

■ Applications

- Consumer Electronics
- Compute and Storage
- Wireless Communications
- Industrial Control Systems
- Automotive System

■ Low Cost Migration Path

- Migration from the Flash based MachXO3LF to the NVCM based MachXO3L
- Pin compatible and equivalent timing

and oscillators dynamically. These features help manage static and dynamic power consumption resulting in low static power for all members of the family.

The MachXO3L/LF devices are available in two versions C and E with two speed grades: -5 and -6, with -6 being the fastest. C devices have an internal linear voltage regulator which supports external VCC supply voltages of 3.3 V or 2.5 V. E devices only accept 1.2 V as the external VCC supply voltage. With the exception of power supply voltage both C and E are functionally compatible with each other.

The MachXO3L/LF PLDs are available in a broad range of advanced halogen-free packages ranging from the space saving 2.5 x 2.5 mm WLCSP to the 19 x 19 mm caBGA. MachXO3L/LF devices support density migration within the same package. Table 1-1 shows the LUT densities, package and I/O options, along with other key parameters.

The MachXO3L/LF devices offer enhanced I/O features such as drive strength control, slew rate control, PCI compatibility, bus-keeper latches, pull-up resistors, pull-down resistors, open drain outputs and hot socketing. Pull-up, pull-down and bus-keeper features are controllable on a “per-pin” basis.

A user-programmable internal oscillator is included in MachXO3L/LF devices. The clock output from this oscillator may be divided by the timer/counter for use as clock input in functions such as LED control, key-board scanner and similar state machines.

The MachXO3L/LF devices also provide flexible, reliable and secure configuration from on-chip NVCM/Flash. These devices can also configure themselves from external SPI Flash or be configured by an external master through the JTAG test access port or through the I²C port. Additionally, MachXO3L/LF devices support dual-boot capability (using external Flash memory) and remote field upgrade (TransFR) capability.

Lattice provides a variety of design tools that allow complex designs to be efficiently implemented using the MachXO3L/LF family of devices. Popular logic synthesis tools provide synthesis library support for MachXO3L/LF. Lattice design tools use the synthesis tool output along with the user-specified preferences and constraints to place and route the design in the MachXO3L/LF device. These tools extract the timing from the routing and back-annotate it into the design for timing verification.

Lattice provides many pre-engineered IP (Intellectual Property) LatticeCORE™ modules, including a number of reference designs licensed free of charge, optimized for the MachXO3L/LF PLD family. By using these configurable soft core IP cores as standardized blocks, users are free to concentrate on the unique aspects of their design, increasing their productivity.

Figure 2-6. Secondary High Fanout Nets for MachXO3L/LF Devices



sysCLOCK Phase Locked Loops (PLLs)

The sysCLOCK PLLs provide the ability to synthesize clock frequencies. All MachXO3L/LF devices have one or more sysCLOCK PLL. CLKI is the reference frequency input to the PLL and its source can come from an external I/O pin or from internal routing. CLKFB is the feedback signal to the PLL which can come from internal routing or an external I/O pin. The feedback divider is used to multiply the reference frequency and thus synthesize a higher frequency clock output.

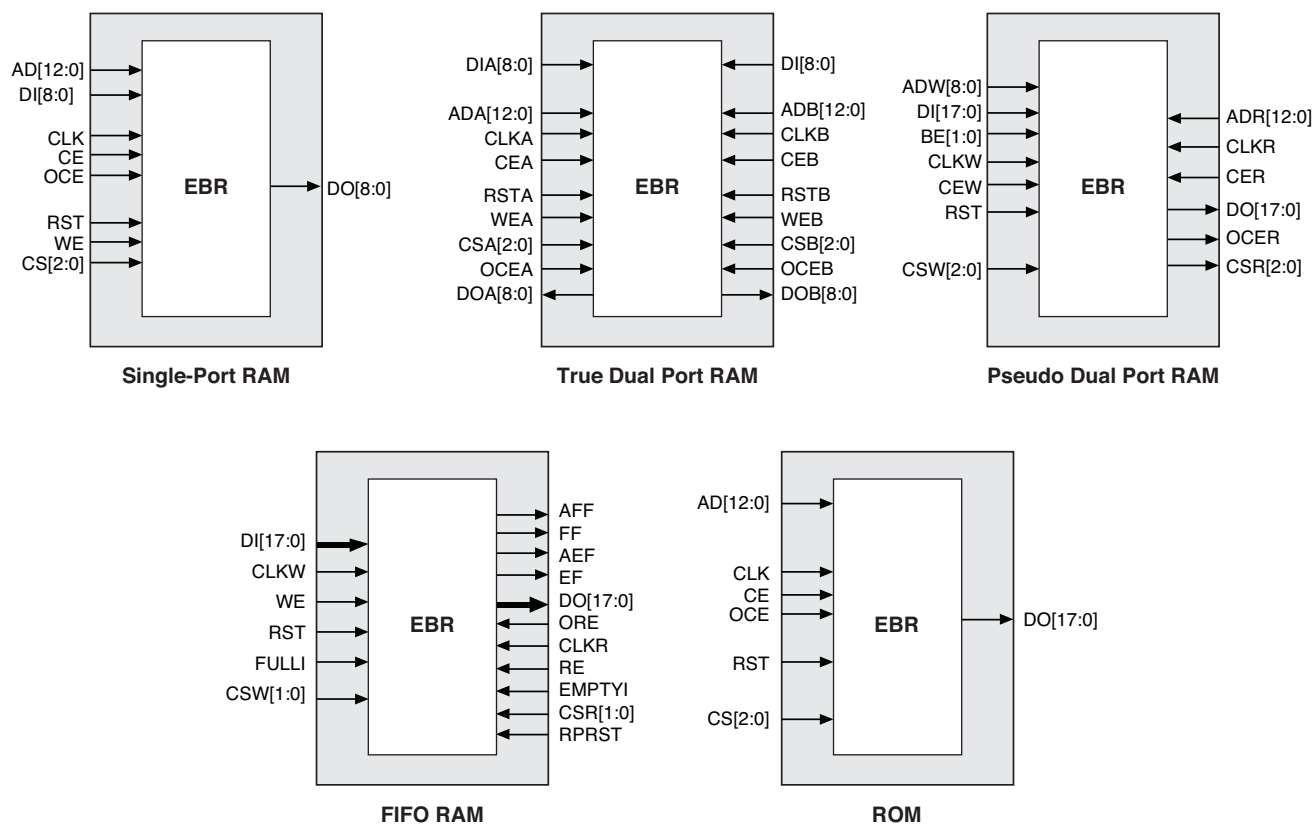
The MachXO3L/LF sysCLOCK PLLs support high resolution (16-bit) fractional-N synthesis. Fractional-N frequency synthesis allows the user to generate an output clock which is a non-integer multiple of the input frequency. For more information about using the PLL with Fractional-N synthesis, please see TN1282, [MachXO3 sysCLOCK PLL Design and Usage Guide](#).

Each output has its own output divider, thus allowing the PLL to generate different frequencies for each output. The output dividers can have a value from 1 to 128. The output dividers may also be cascaded together to generate low frequency clocks. The CLKOP, CLKOS, CLKOS2, and CLKOS3 outputs can all be used to drive the MachXO3L/LF clock distribution network directly or general purpose routing resources can be used.

The LOCK signal is asserted when the PLL determines it has achieved lock and de-asserted if a loss of lock is detected. A block diagram of the PLL is shown in Figure 2-7.

The setup and hold times of the device can be improved by programming a phase shift into the CLKOS, CLKOS2, and CLKOS3 output clocks which will advance or delay the output clock with reference to the CLKOP output clock.

Figure 2-8. sysMEM Memory Primitives



Output Register Block

The output register block registers signals from the core of the device before they are passed to the sysIO buffers.

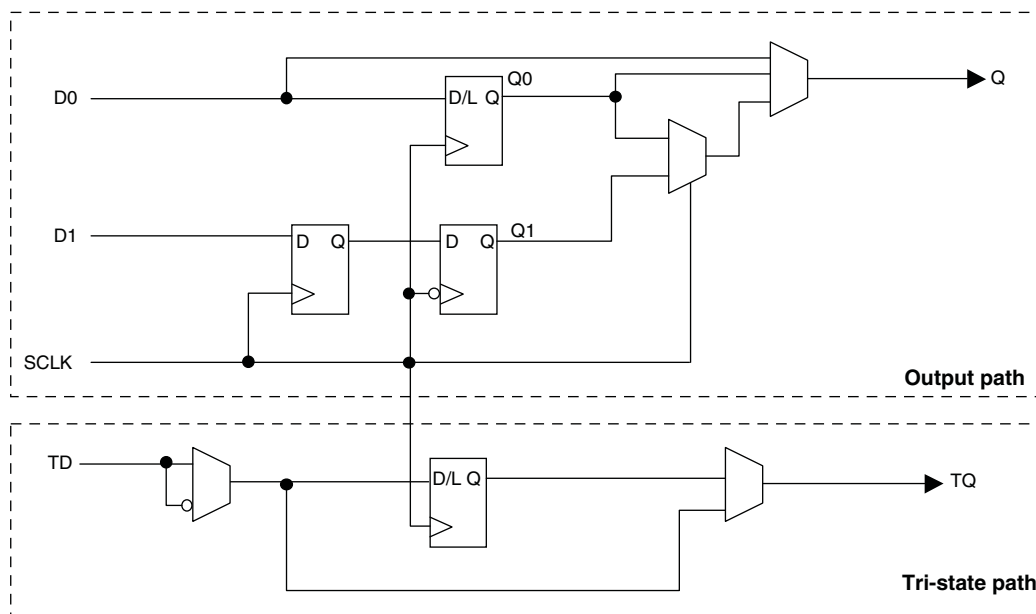
Left, Top, Bottom Edges

In SDR mode, D0 feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as a D-type register or latch.

In DDR generic mode, D0 and D1 inputs are fed into registers on the positive edge of the clock. At the next falling edge the registered D1 input is registered into the register Q1. A multiplexer running off the same clock is used to switch the mux between the outputs of registers Q0 and Q1 that will then feed the output.

Figure 2-12 shows the output register block on the left, top and bottom edges.

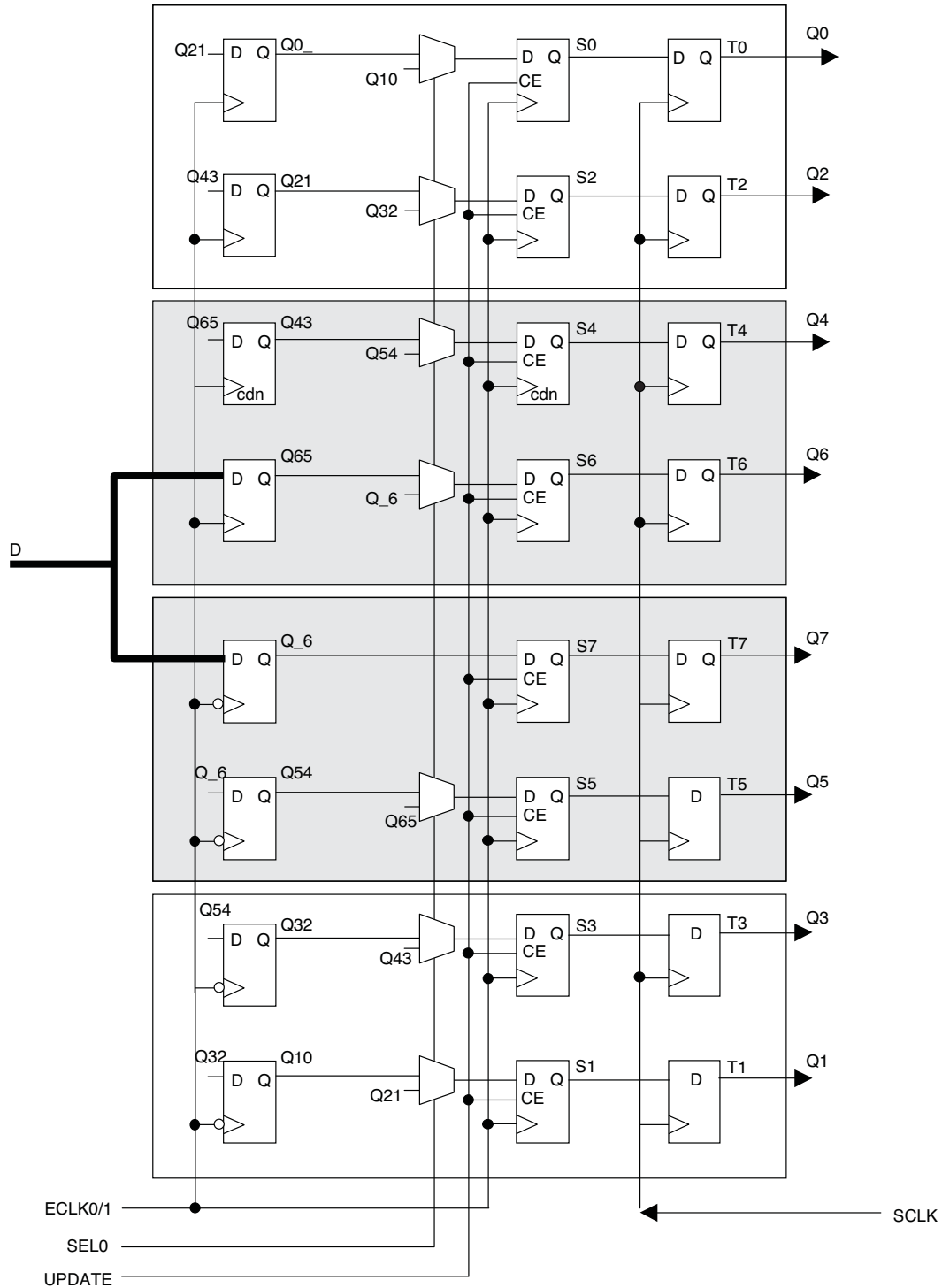
Figure 2-12. MachXO3L/LF Output Register Block Diagram (PIO on the Left, Top and Bottom Edges)



Tri-state Register Block

The tri-state register block registers tri-state control signals from the core of the device before they are passed to the sysIO buffers. The block contains a register for SDR operation. In SDR, TD input feeds one of the flip-flops that then feeds the output.

Figure 2-13. Input Gearbox



More information on the input gearbox is available in TN1281, [Implementing High-Speed Interfaces with MachXO3 Devices](#).

For more details on these embedded functions, please refer to TN1293, [Using Hardened Control Functions in MachXO3 Devices](#).

User Flash Memory (UFM)

MachXO3LF devices provide a User Flash Memory block, which can be used for a variety of applications including storing a portion of the configuration image, initializing EBRs, to store PROM data or, as a general purpose user Flash memory. The UFM block connects to the device core through the embedded function block WISHBONE interface. Users can also access the UFM block through the JTAG, I2C and SPI interfaces of the device. The UFM block offers the following features:

- Non-volatile storage up to 256 kbits
- 100K write cycles
- Write access is performed page-wise; each page has 128 bits (16 bytes)
- Auto-increment addressing
- WISHBONE interface

For more information on the UFM, please refer to TN1293, [Using Hardened Control Functions in MachXO3 Devices](#).

Standby Mode and Power Saving Options

MachXO3L/LF devices are available in two options, the C and E devices. The C devices have a built-in voltage regulator to allow for 2.5 V V_{CC} and 3.3 V V_{CC} while the E devices operate at 1.2 V V_{CC} .

MachXO3L/LF devices have been designed with features that allow users to meet the static and dynamic power requirements of their applications by controlling various device subsystems such as the bandgap, power-on-reset circuitry, I/O bank controllers, power guard, on-chip oscillator, PLLs, etc. In order to maximize power savings, MachXO3L/LF devices support a low power Stand-by mode.

In the stand-by mode the MachXO3L/LF devices are powered on and configured. Internal logic, I/Os and memories are switched on and remain operational, as the user logic waits for an external input. The device enters this mode when the standby input of the standby controller is toggled or when an appropriate I²C or JTAG instruction is issued by an external master. Various subsystems in the device such as the band gap, power-on-reset circuitry etc can be configured such that they are automatically turned “off” or go into a low power consumption state to save power when the device enters this state. Note that the MachXO3L/LF devices are powered on when in standby mode and all power supplies should remain in the Recommended Operating Conditions.

Configuration and Testing

This section describes the configuration and testing features of the MachXO3L/LF family.

IEEE 1149.1-Compliant Boundary Scan Testability

All MachXO3L/LF devices have boundary scan cells that are accessed through an IEEE 1149.1 compliant test access port (TAP). This allows functional testing of the circuit board, on which the device is mounted, through a serial scan path that can access all critical logic nodes. Internal registers are linked internally, allowing test data to be shifted in and loaded directly onto test nodes, or test data to be captured and shifted out for verification. The test access port consists of dedicated I/Os: TDI, TDO, TCK and TMS. The test access port shares its power supply with V_{CCIO} Bank 0 and can operate with LVCMOS3.3, 2.5, 1.8, 1.5, and 1.2 standards.

For more details on boundary scan test, see AN8066, [Boundary Scan Testability with Lattice sysIO Capability](#) and TN1087, [Minimizing System Interruption During Configuration Using TransFR Technology](#).

Device Configuration

All MachXO3L/LF devices contain two ports that can be used for device configuration. The Test Access Port (TAP), which supports bit-wide configuration and the sysCONFIG port which supports serial configuration through I²C or SPI. The TAP supports both the IEEE Standard 1149.1 Boundary Scan specification and the IEEE Standard 1532 In-System Configuration specification. There are various ways to configure a MachXO3L/LF device:

1. Internal NVCM/Flash Download
2. JTAG
3. Standard Serial Peripheral Interface (Master SPI mode) – interface to boot PROM memory
4. System microprocessor to drive a serial slave SPI port (SSPI mode)
5. Standard I²C Interface to system microprocessor

Upon power-up, the configuration SRAM is ready to be configured using the selected sysCONFIG port. Once a configuration port is selected, it will remain active throughout that configuration cycle. The IEEE 1149.1 port can be activated any time after power-up by sending the appropriate command through the TAP port. Optionally the device can run a CRC check upon entering the user mode. This will ensure that the device was configured correctly.

The sysCONFIG port has 10 dual-function pins which can be used as general purpose I/Os if they are not required for configuration. See TN1279, [MachXO3 Programming and Configuration Usage Guide](#) for more information about using the dual-use pins as general purpose I/Os.

Lattice design software uses proprietary compression technology to compress bit-streams for use in MachXO3L/LF devices. Use of this technology allows Lattice to provide a lower cost solution. In the unlikely event that this technology is unable to compress bitstreams to fit into the amount of on-chip NVCM/Flash, there are a variety of techniques that can be utilized to allow the bitstream to fit in the on-chip NVCM/Flash. For more details, refer to TN1279, [MachXO3 Programming and Configuration Usage Guide](#).

The Test Access Port (TAP) has five dual purpose pins (TDI, TDO, TMS, TCK and JTAGENB). These pins are dual function pins - TDI, TDO, TMS and TCK can be used as general purpose I/O if desired. For more details, refer to TN1279, [MachXO3 Programming and Configuration Usage Guide](#).

TransFR (Transparent Field Reconfiguration)

TransFR is a unique Lattice technology that allows users to update their logic in the field without interrupting system operation using a simple push-button solution. For more details refer to TN1087, [Minimizing System Interruption During Configuration Using TransFR Technology](#) for details.

TraceID

Each MachXO3L/LF device contains a unique (per device), TraceID that can be used for tracking purposes or for IP security applications. The TraceID is 64 bits long. Eight out of 64 bits are user-programmable, the remaining 56 bits are factory-programmed. The TraceID is accessible through the EFB WISHBONE interface and can also be accessed through the SPI, I²C, or JTAG interfaces.

Density Shifting

The MachXO3L/LF family has been designed to enable density migration within the same package. Furthermore, the architecture ensures a high success rate when performing design migration from lower density devices to higher density devices. In many cases, it is also possible to shift a lower utilization design targeted for a high-density device to a lower density device. However, the exact details of the final resource utilization will impact the likely success in each case. When migrating from lower to higher density or higher to lower density, ensure to review all the power supplies and NC pins of the chosen devices. For more details refer to the [MachXO3 migration files](#).

Power-On-Reset Voltage Levels^{1, 2, 3, 4, 5}

Symbol	Parameter	Min.	Typ.	Max.	Units
V_{PORUP}	Power-On-Reset ramp up trip point (band gap based circuit monitoring V_{CCINT} and V_{CCIO0})	0.9	—	1.06	V
$V_{PORUPEXT}$	Power-On-Reset ramp up trip point (band gap based circuit monitoring external V_{CC} power supply)	1.5	—	2.1	V
$V_{PORDNBG}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CCINT})	0.75	—	0.93	V
$V_{PORDNBGEXT}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CC})	0.98	—	1.33	V
$V_{PORDNSRAM}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CCINT})	—	0.6	—	V
$V_{PORDNSRAMEXT}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CC})	—	0.96	—	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.
2. For devices without voltage regulators V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage.
3. Note that V_{PORUP} (min.) and $V_{PORDNBG}$ (max.) are in different process corners. For any given process corner $V_{PORDNBG}$ (max.) is always 12.0 mV below V_{PORUP} (min.).
4. $V_{PORUPEXT}$ is for C devices only. In these devices a separate POR circuit monitors the external V_{CC} power supply.
5. V_{CCIO0} does not have a Power-On-Reset ramp down trip point. V_{CCIO0} must remain within the Recommended Operating Conditions to ensure proper operation.

Hot Socketing Specifications^{1, 2, 3}

Symbol	Parameter	Condition	Max.	Units
I_{DK}	Input or I/O leakage Current	$0 < V_{IN} < V_{IH}$ (MAX)	+/-1000	μA

1. Insensitive to sequence of V_{CC} and V_{CCIO} . However, assumes monotonic rise/fall rates for V_{CC} and V_{CCIO} .
2. $0 < V_{CC} < V_{CC}$ (MAX), $0 < V_{CCIO} < V_{CCIO}$ (MAX).
3. I_{DK} is additive to I_{PU} , I_{PD} or I_{BH} .

ESD Performance

Please refer to the [MachXO2 Product Family Qualification Summary](#) for complete qualification data, including ESD performance.

Static Supply Current – C/E Devices^{1, 2, 3, 6}

Symbol	Parameter	Device	Typ. ⁴	Units
I _{CC}	Core Power Supply	LCMXO3L/LF-1300C 256 Ball Package	4.8	mA
		LCMXO3L/LF-2100C	4.8	mA
		LCMXO3L/LF-2100C 324 Ball Package	8.45	mA
		LCMXO3L/LF-4300C	8.45	mA
		LCMXO3L/LF-4300C 400 Ball Package	12.87	mA
		LCMXO3L/LF-6900C ⁷	12.87	mA
		LCMXO3L/LF-9400C ⁷	17.86	mA
		LCMXO3L/LF-640E	1.00	mA
		LCMXO3L/LF-1300E	1.00	mA
		LCMXO3L/LF-1300E 256 Ball Package	1.39	mA
		LCMXO3L/LF-2100E	1.39	mA
		LCMXO3L/LF-2100E 324 Ball Package	2.55	mA
		LCMXO3L/LF-4300E	2.55	mA
		LCMXO3L/LF-6900E	4.06	mA
		LCMXO3L/LF-9400E	5.66	mA
I _{CCIO}	Bank Power Supply ⁵ V _{CCIO} = 2.5 V	All devices	0	mA

1. For further information on supply current, please refer to TN1289, [Power Estimation and Management for MachXO3 Devices](#).

2. Assumes blank pattern with the following characteristics: all outputs are tri-stated, all inputs are configured as LVCMOS and held at V_{CCIO} or GND, on-chip oscillator is off, on-chip PLL is off.

3. Frequency = 0 MHz.

4. T_J = 25 °C, power supplies at nominal voltage.

5. Does not include pull-up/pull-down.

6. To determine the MachXO3L/LF peak start-up current data, use the Power Calculator tool.

7. Determination of safe ambient operating conditions requires use of the Diamond Power Calculator tool.

sysIO Single-Ended DC Electrical Characteristics^{1, 2}

Input/Output Standard	V _{IL}		V _{IH}		V _{OL} Max. (V)	V _{OH} Min. (V)	I _{OL} Max. ⁴ (mA)	I _{OH} Max. ⁴ (mA)
	Min. (V) ³	Max. (V)	Min. (V)	Max. (V)				
LVCMOS 3.3 LVTTL	-0.3	0.8	2.0	3.6	0.4	V _{CCIO} - 0.4	4	-4
							8	-8
							12	-12
							16	-16
LVCMOS 2.5	-0.3	0.7	1.7	3.6	0.4	V _{CCIO} - 0.4	0.1	-0.1
							4	-4
							8	-8
							12	-12
LVCMOS 1.8	-0.3	0.35V _{CCIO}	0.65V _{CCIO}	3.6	0.4	V _{CCIO} - 0.4	0.1	-0.1
							4	-4
							8	-8
							12	-12
LVCMOS 1.5	-0.3	0.35V _{CCIO}	0.65V _{CCIO}	3.6	0.4	V _{CCIO} - 0.4	0.1	-0.1
							4	-4
							8	-8
							12	-12
LVCMOS 1.2	-0.3	0.35V _{CCIO}	0.65V _{CCIO}	3.6	0.4	V _{CCIO} - 0.4	0.1	-0.1
							4	-2
							8	-6
							12	-12
LVCMOS25R33	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS18R33	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS18R25	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS15R33	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS15R25	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS12R33	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS12R25	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain
LVCMOS10R33	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS10R25	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain

1. MachXO3L/LF devices allow LVCMOS inputs to be placed in I/O banks where V_{CCIO} is different from what is specified in the applicable JEDEC specification. This is referred to as a ratioed input buffer. In a majority of cases this operation follows or exceeds the applicable JEDEC specification. The cases where MachXO3L/LF devices do not meet the relevant JEDEC specification are documented in the table below.
2. MachXO3L/LF devices allow for LVCMOS referenced I/Os which follow applicable JEDEC specifications. For more details about mixed mode operation please refer to please refer to TN1280, [MachXO3 sysIO Usage Guide](#).
3. The dual function I²C pins SCL and SDA are limited to a V_{IL} min of -0.25 V or to -0.3 V with a duration of <10 ns.
4. For electromigration, the average DC current sourced or sinked by I/O pads between two consecutive V_{CCIO} or GND pad connections, or between the last V_{CCIO} or GND in an I/O bank and the end of an I/O bank, as shown in the Logic Signal Connections table (also shown as I/O grouping) shall not exceed a maximum of n * 8 mA. "n" is the number of I/O pads between the two consecutive bank V_{CCIO} or GND connections or between the last V_{CCIO} and GND in a bank and the end of a bank. IO Grouping can be found in the Data Sheet Pin Tables, which can also be generated from the Lattice Diamond software.

Table 3-5. MIPI D-PHY Output DC Conditions¹

	Description	Min.	Typ.	Max.	Units
Transmitter					
External Termination					
RL	1% external resistor with VCCIO = 2.5 V	—	50	—	Ohms
	1% external resistor with VCCIO = 3.3 V	—	50	—	
RH	1% external resistor with performance up to 800 Mbps or with performance up 900 Mbps when VCCIO = 2.5 V	—	330	—	Ohms
	1% external resistor with performance between 800 Mbps to 900 Mbps when VCCIO = 3.3 V	—	464	—	Ohms
High Speed					
VCCIO	VCCIO of the Bank with LVDS Emulated output buffer	—	2.5	—	V
	VCCIO of the Bank with LVDS Emulated output buffer	—	3.3	—	V
VCMTX	HS transmit static common mode voltage	150	200	250	mV
VOD	HS transmit differential voltage	140	200	270	mV
VOHHS	HS output high voltage	—	—	360	V
ZOS	Single ended output impedance	—	50	—	Ohms
ΔZOS	Single ended output impedance mismatch	—	—	10	%
Low Power					
VCCIO	VCCIO of the Bank with LVCMOS12D 6 mA drive bidirectional IO buffer	—	1.2	—	V
VOH	Output high level	1.1	1.2	1.3	V
VOL	Output low level	–50	0	50	mV
ZOLP	Output impedance of LP transmitter	110	—	—	Ohms

¹. Over Recommended Operating Conditions

Figure 3-6. Receiver GDDR71_RX. Waveforms

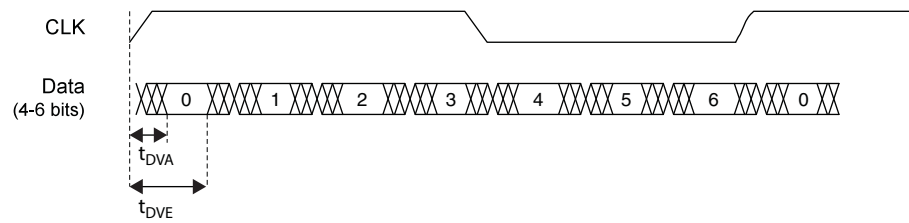
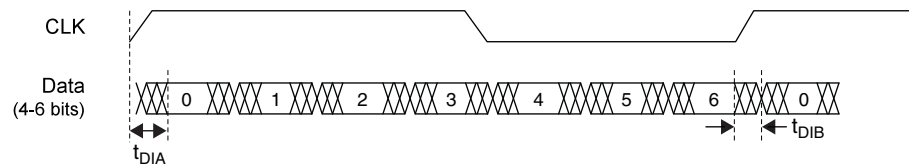


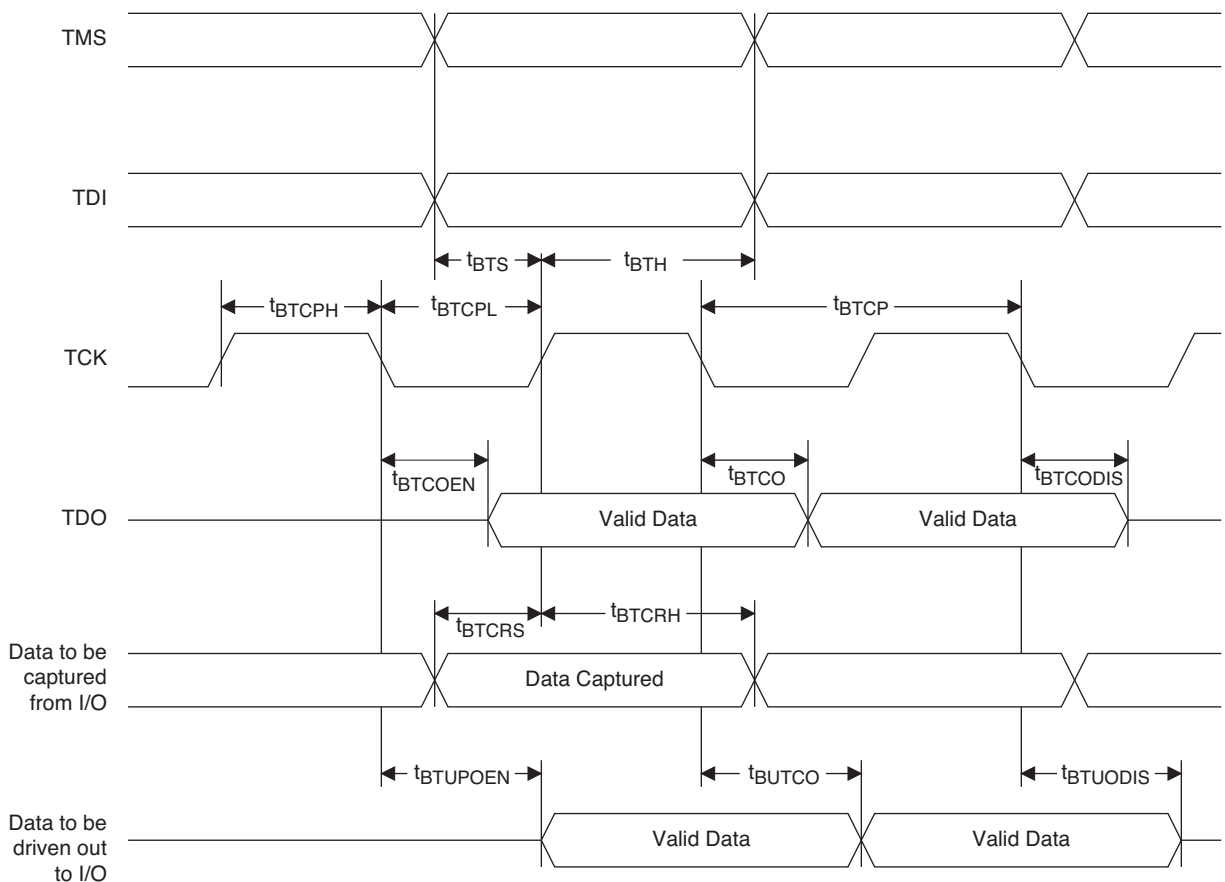
Figure 3-7. Transmitter GDDR71_TX. Waveforms



JTAG Port Timing Specifications

Symbol	Parameter	Min.	Max.	Units
f_{MAX}	TCK clock frequency	—	25	MHz
t_{BTCPH}	TCK [BSCAN] clock pulse width high	20	—	ns
t_{BTCPL}	TCK [BSCAN] clock pulse width low	20	—	ns
t_{BTS}	TCK [BSCAN] setup time	10	—	ns
t_{BTH}	TCK [BSCAN] hold time	8	—	ns
t_{BTCO}	TAP controller falling edge of clock to valid output	—	10	ns
$t_{BTCODIS}$	TAP controller falling edge of clock to valid disable	—	10	ns
t_{BTCOEN}	TAP controller falling edge of clock to valid enable	—	10	ns
t_{BTCRS}	BSCAN test capture register setup time	8	—	ns
t_{BTCRH}	BSCAN test capture register hold time	20	—	ns
t_{BUTCO}	BSCAN test update register, falling edge of clock to valid output	—	25	ns
$t_{BTUODIS}$	BSCAN test update register, falling edge of clock to valid disable	—	25	ns
$t_{BTUPOEN}$	BSCAN test update register, falling edge of clock to valid enable	—	25	ns

Figure 3-8. JTAG Port Timing Waveforms



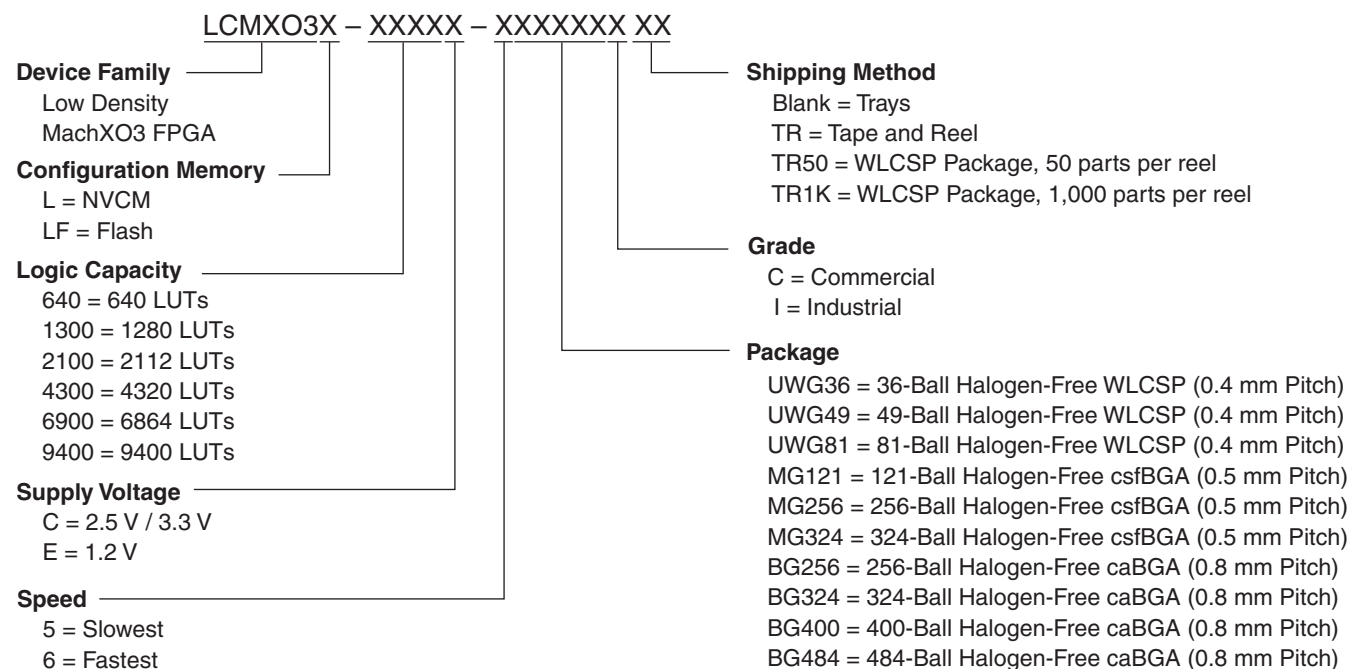
sysCONFIG Port Timing Specifications

Symbol	Parameter		Min.	Max.	Units
All Configuration Modes					
t _{PRGM}	PROGRAMN low pulse accept		55	—	ns
t _{PRGMJ}	PROGRAMN low pulse rejection		—	25	ns
t _{INITL}	INITN low time	LCMXO3L/LF-640/ LCMXO3L/LF-1300	—	55	us
		LCMXO3L/LF-1300 256-Ball Package/ LCMXO3L/LF-2100	—	70	us
		LCMXO3L/LF-2100 324-Ball Package/ LCMXO3-4300	—	105	us
		LCMXO3L/LF-4300 400-Ball Package/ LCMXO3-6900	—	130	us
		LCMXO3L/LF-9400C	—	175	us
t _{DPPINIT}	PROGRAMN low to INITN low		—	150	ns
t _{DPPDONE}	PROGRAMN low to DONE low		—	150	ns
t _{IODISS}	PROGRAMN low to I/O disable		—	120	ns
Slave SPI					
f _{MAX}	CCLK clock frequency		—	66	MHz
t _{CCLKH}	CCLK clock pulse width high		7.5	—	ns
t _{CCLKL}	CCLK clock pulse width low		7.5	—	ns
t _{STSU}	CCLK setup time		2	—	ns
t _{STH}	CCLK hold time		0	—	ns
t _{STCO}	CCLK falling edge to valid output		—	10	ns
t _{STOZ}	CCLK falling edge to valid disable		—	10	ns
t _{STOV}	CCLK falling edge to valid enable		—	10	ns
t _{SCS}	Chip select high time		25	—	ns
t _{SCSS}	Chip select setup time		3	—	ns
t _{SCSH}	Chip select hold time		3	—	ns
Master SPI					
f _{MAX}	MCLK clock frequency		—	133	MHz
t _{MCLKH}	MCLK clock pulse width high		3.75	—	ns
t _{MCLKL}	MCLK clock pulse width low		3.75	—	ns
t _{STSU}	MCLK setup time		5	—	ns
t _{STH}	MCLK hold time		1	—	ns
t _{CSSPI}	INITN high to chip select low		100	200	ns
t _{MCLK}	INITN high to first MCLK edge		0.75	1	us

	MachXO3L/LF-4300						
	WLCSP81	CSFBGA121	CSFBGA256	CSFBGA324	CABGA256	CABGA324	CABGA400
General Purpose IO per Bank							
Bank 0	29	24	50	71	50	71	83
Bank 1	0	26	52	62	52	68	84
Bank 2	20	26	52	72	52	72	84
Bank 3	7	7	16	22	16	24	28
Bank 4	0	7	16	14	16	16	24
Bank 5	7	10	20	27	20	28	32
Total General Purpose Single Ended IO	63	100	206	268	206	279	335
Differential IO per Bank							
Bank 0	15	12	25	36	25	36	42
Bank 1	0	13	26	30	26	34	42
Bank 2	10	13	26	36	26	36	42
Bank 3	3	3	8	10	8	12	14
Bank 4	0	3	8	6	8	8	12
Bank 5	3	5	10	13	10	14	16
Total General Purpose Differential IO	31	49	103	131	103	140	168
Dual Function IO	25	37	37	37	37	37	37
Number 7:1 or 8:1 Gearboxes							
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	10	7	18	18	18	18	21
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	10	13	18	18	18	18	21
High-speed Differential Outputs							
Bank 0	10	7	18	18	18	18	21
VCCIO Pins							
Bank 0	3	1	4	4	4	4	5
Bank 1	0	1	3	4	4	4	5
Bank 2	2	1	4	4	4	4	5
Bank 3	1	1	2	2	1	2	2
Bank 4	0	1	2	2	2	2	2
Bank 5	1	1	2	2	1	2	2
VCC	4	4	8	8	8	10	10
GND	6	10	24	16	24	16	33
NC	0	0	0	13	1	0	0
Reserved for Configuration	1	1	1	1	1	1	1
Total Count of Bonded Pins	81	121	256	324	256	324	400

	MachXO3L/LF-6900				
	CSFBGA256	CSFBGA324	CABGA256	CABGA324	CABGA400
General Purpose IO per Bank					
Bank 0	50	73	50	71	83
Bank 1	52	68	52	68	84
Bank 2	52	72	52	72	84
Bank 3	16	24	16	24	28
Bank 4	16	16	16	16	24
Bank 5	20	28	20	28	32
Total General Purpose Single Ended IO	206	281	206	279	335
Differential IO per Bank					
Bank 0	25	36	25	36	42
Bank 1	26	34	26	34	42
Bank 2	26	36	26	36	42
Bank 3	8	12	8	12	14
Bank 4	8	8	8	8	12
Bank 5	10	14	10	14	16
Total General Purpose Differential IO	103	140	103	140	168
Dual Function IO	37	37	37	37	37
Number 7:1 or 8:1 Gearboxes					
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	20	21	20	21	21
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	20	21	20	21	21
High-speed Differential Outputs					
Bank 0	20	21	20	21	21
VCCIO Pins					
Bank 0	4	4	4	4	5
Bank 1	3	4	4	4	5
Bank 2	4	4	4	4	5
Bank 3	2	2	1	2	2
Bank 4	2	2	2	2	2
Bank 5	2	2	1	2	2
VCC	8	8	8	10	10
GND	24	16	24	16	33
NC	0	0	1	0	0
Reserved for Configuration	1	1	1	1	1
Total Count of Bonded Pins	256	324	256	324	400

MachXO3 Part Number Description



Ordering Information

MachXO3L/LF devices have top-side markings as shown in the examples below, on the 256-Ball caBGA package with MachXO3-6900 device in Commercial Temperature in Speed Grade 5. Notice that for the MachXO3LF device, *LMXO3LF* is used instead of *LCMXO3LF* as in the Part Number.



Note: *LCMXO3LF* is marked with *LMXO3LF*

Note: Markings are abbreviated for small packages.

MachXO3LF Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-640E-5MG121C	640	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3LF-640E-6MG121C	640	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3LF-640E-5MG121I	640	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3LF-640E-6MG121I	640	1.2 V	6	Halogen-Free csfBGA	121	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-1300E-5UWG36CTR	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3LF-1300E-5UWG36CTR50	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3LF-1300E-5UWG36CTR1K	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3LF-1300E-5UWG36ITR	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3LF-1300E-5UWG36ITR50	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3LF-1300E-5UWG36ITR1K	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3LF-1300E-5MG121C	1300	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3LF-1300E-6MG121C	1300	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3LF-1300E-5MG121I	1300	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3LF-1300E-6MG121I	1300	1.2 V	6	Halogen-Free csfBGA	121	IND
LCMXO3LF-1300E-5MG256C	1300	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3LF-1300E-6MG256C	1300	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3LF-1300E-5MG256I	1300	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3LF-1300E-6MG256I	1300	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3LF-1300C-5BG256C	1300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3LF-1300C-6BG256C	1300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3LF-1300C-5BG256I	1300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3LF-1300C-6BG256I	1300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-2100E-5UWG49CTR	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3LF-2100E-5UWG49CTR50	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3LF-2100E-5UWG49CTR1K	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3LF-2100E-5UWG49ITR	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3LF-2100E-5UWG49ITR50	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3LF-2100E-5UWG49ITR1K	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3LF-2100E-5MG121C	2100	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3LF-2100E-6MG121C	2100	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3LF-2100E-5MG121I	2100	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3LF-2100E-6MG121I	2100	1.2 V	6	Halogen-Free csfBGA	121	IND
LCMXO3LF-2100E-5MG256C	2100	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3LF-2100E-6MG256C	2100	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3LF-2100E-5MG256I	2100	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3LF-2100E-6MG256I	2100	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3LF-2100E-5MG324C	2100	1.2 V	5	Halogen-Free csfBGA	324	COM
LCMXO3LF-2100E-6MG324C	2100	1.2 V	6	Halogen-Free csfBGA	324	COM
LCMXO3LF-2100E-5MG324I	2100	1.2 V	5	Halogen-Free csfBGA	324	IND